## TOSHIBA

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

### RN1901FE,RN1902FE,RN1903FE RN1904FE,RN1905FE,RN1906FE

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications.

- Two devices are incorporated into an Extreme-Super-Mini (6 pin) package.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.
- Complementary to RN2901FE~RN2906FE

#### **Equivalent Circuit and Bias Resistor Values**



Type No.	R1 (kΩ)	R2 (kΩ)
RN1901FE	4.7	4.7
RN1902FE	10	10
RN1903FE	22	22
RN1904FE	47	47
RN1905FE	2.2	47
RN1906FE	4.7	47

 $1.6 \pm 0.05$ 1.2±0.05 6 0.5 .0±0.05 I.6±0.05 0.2±0.05 5 0.5 2 ٦ 80 0.55±0 0.12±0.05 1. EMITTER1 (E1) 2. BASE1 (B1) 3. COLLECTOR2 (C2) 4. EMITTER2 (E2) 5. BASE2 (B2) 6. COLLECTOR1 (C1) ES6 JEDEC \_ JEITA TOSHIBA \_

Weight: g (typ.)

#### Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage	RN1901FE~	V <sub>CBO</sub>	50	V	
Collector-emitter voltage	RN1906FE	V <sub>CEO</sub>	50	V	
Emitter base voltage	RN1901FE~ RN1904FE		10	V	
Emitter-base voltage	RN1905FE, RN1906FE	V <sub>EBO</sub>	5		
Collector current		Ι <sub>C</sub>	100	mA	
Collector power dissipation	RN1901FE~	P <sub>C</sub> (Note)	100	mW	
Junction temperature	RN1906FE T <sub>j</sub>		150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

Note: Total rating

# Equivalent Circuit (top view)



Unit: mm

## Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	RN1901FE~1906FE	I <sub>CBO</sub>	$V_{CB} = 50 \text{ V}, \text{ I}_{E} = 0$			100	nA
		I <sub>CEO</sub>	$V_{CE} = 50 \text{ V}, \text{ I}_{B} = 0$			500	nA
Emitter cut-off current	RN1901FE	IEBO	V <sub>EB</sub> = 10 V, I <sub>C</sub> = 0	0.82	_	1.52	mA
	RN1902FE			0.38		0.71	
	RN1903FE			0.17		0.33	
	RN1904FE			0.082		0.15	
	RN1905FE		$V_{EB} = 5 V, I_{C} = 0$	0.078		0.145	
	RN1906FE			0.074		0.138	
	RN1901FE			30			
	RN1902FE			50			
DC ourrent goin	RN1903FE		$\lambda = 5 \lambda = 10 m \Lambda$	70			
DC current gain	RN1904FE	h <sub>FE</sub>	$V_{CE} = 5 V, I_C = 10 mA$	80			
	RN1905FE			80			
	RN1906FE	-		80			
Collector-emitter saturation voltage	RN1901FE~1906FE	V <sub>CE (sat)</sub>	$I_C = 5 \text{ mA},$ $I_B = 0.25 \text{ mA}$	_	0.1	0.3	V
Input voltage (ON)	RN1901FE	VI (ON)	$V_{CE} = 0.2 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	1.1		2.0	V
	RN1902FE			1.2		2.4	
	RN1903FE			1.3		3.0	
	RN1904FE			1.5		5.0	
	RN1905FE			0.6		1.1	
	RN1906FE			0.7		1.3	
Input voltage (OFF)	RN1901FE~1904FE	VI (OFF)	$V_{CE} = 5 \text{ V}, \text{ I}_{C} = 0.1 \text{ mA}$	1.0		1.5	V
	RN1905FE, 1906FE			0.5		0.8	
Transition frequency	RN1901FE~1906FE	fT	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	_	250		MHz
Collector output capacitance	RN1901FE~1906FE	C <sub>ob</sub>	$\label{eq:VCB} \begin{array}{l} V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \\ f = 1 \text{ MHz} \end{array}$	_	3	6	pF
	RN1901FE	- R1		3.29	4.7	6.11	kΩ
	RN1902FE			7	10	13	
Input resistor	RN1903FE			15.4	22	28.6	
	RN1904FE			32.9	47	61.1	
	RN1905FE			1.54	2.2	2.86	
	RN1906FE			3.29	4.7	6.11	
Resistor ratio	RN1901FE~1904FE		_	0.9	1.0	1.1	
	RN1905FE	R1/R2		0.0421	0.0468	0.0515	
	RN1906FE			0.09	0.1	0.11	

Type Name	Marking
RN1901FE	Type name XA •
RN1902FE	Type name XB
RN1903FE	Type name XC
RN1904FE	Type name X D
RN1905FE	Type name XE
RN1906FE	Type name X F

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